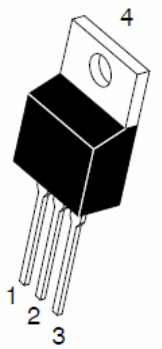
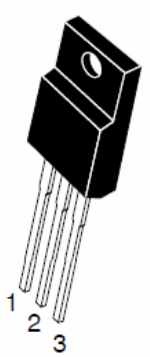
TSR30L150CT
TSR30L150CTF

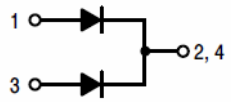
Trench MOS Barrier Schottky Rectifier

TO-220AB
TSR30L150CT



ITO-220AB
TSR30L150CTF





Features
- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

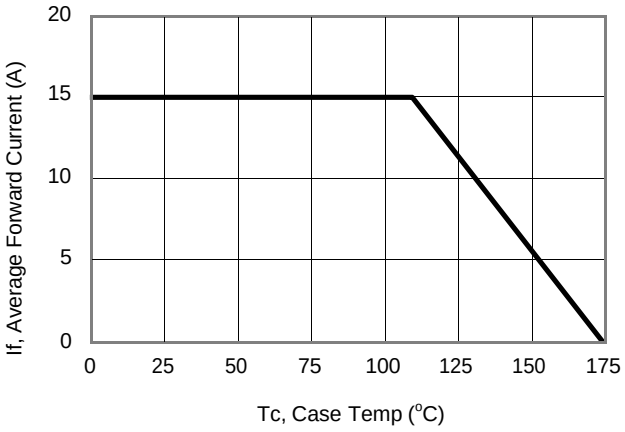
Applications
- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (TJ = 25°C unless otherwise noted)

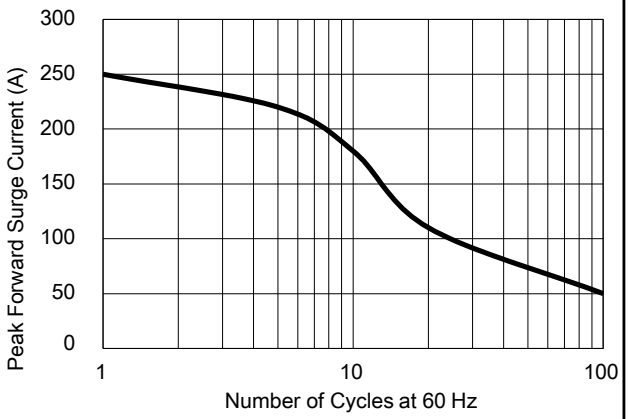
Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage			V_{RRM}	150		V
Maximum average forward rectified current		per device	$I_{F(AV)}$	30		A
		per diode		15		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode			I_{FSM}	220		A
Operating junction and storage temperature range			T_J, T_{STG}	-65 to +150		℃
Typical thermal resistance per leg		TO-220AB	$R_{\theta JC}$	2		°C/W
		ITO-220AB		4		°C/W
Instantaneous forward voltage per diode			$V_{F(1)}$	TYP.	MAX.	
	I_F=3A	T_J=25°C		0.61	-	V
	I_F=3A	T_J=125°C		0.56	-	
	I_F=15A	T_J=25°C		0.77	0.85	
	I_F=15A	T_J=125°C		0.68	-	
Instantaneous reverse current per diode at rated reverse voltage		T_J=25°C	$I_{R(2)}$	10	50	uA
		T_J=125°C		-	1	mA

Notes:
(1) Pulse test: 300 μs pulse width, 1 % duty cycle
(2) Pulse test: Pulse width ≦ 40 ms

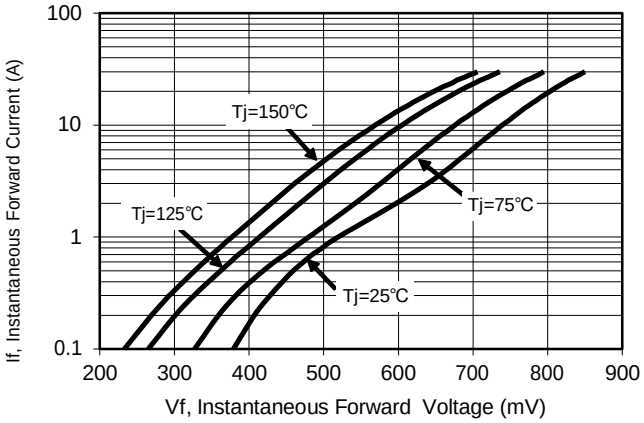
RATINGS AND CHARACTERISTICS CURVES (TA = 25 ˚C unless otherwise noted)



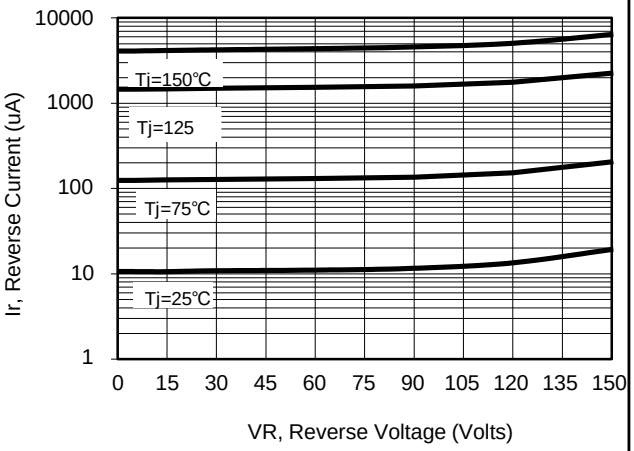
Current Derating, Case



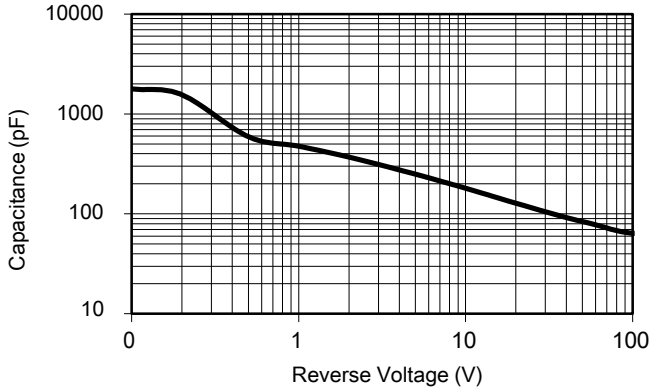
Maximum Repetitive Surge Current



Typical Forward Voltage



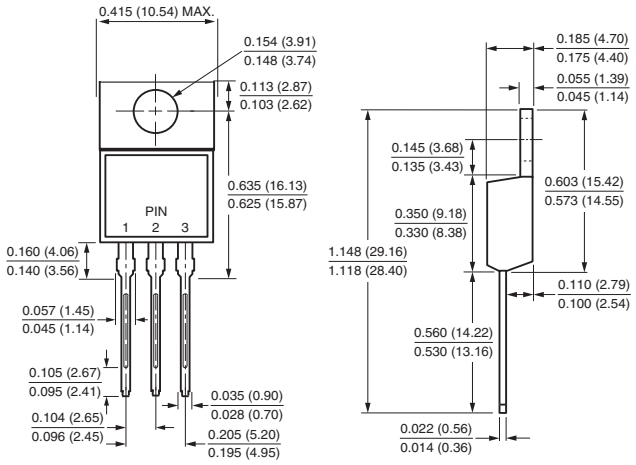
Typical Reverse Current



Typical Junction Capacitance

PACKAGE OUTLINE DIMENSIONS

TO-220AB



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